

MASK FOR CORRECTING LIGHT PROXIMITY EFFECT AND METHOD FOR PRODUCING THE SAME

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Abstract:

PROBLEM TO BE SOLVED: To provide a mask for correcting a light proximity effect and a method for producing the mask. SOLUTION: A dummy pattern is formed in a thin pattern region on a mask by utilizing phase contrast to impart the same shape as the shape of light diffracted by a dense pattern to light diffracted by the thin pattern, thereby reducing the thin-dense deflection of an element pattern formed on a wafer. An overall focus margin can be therefore increased. COPYRIGHT: (C)2003,JPO

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